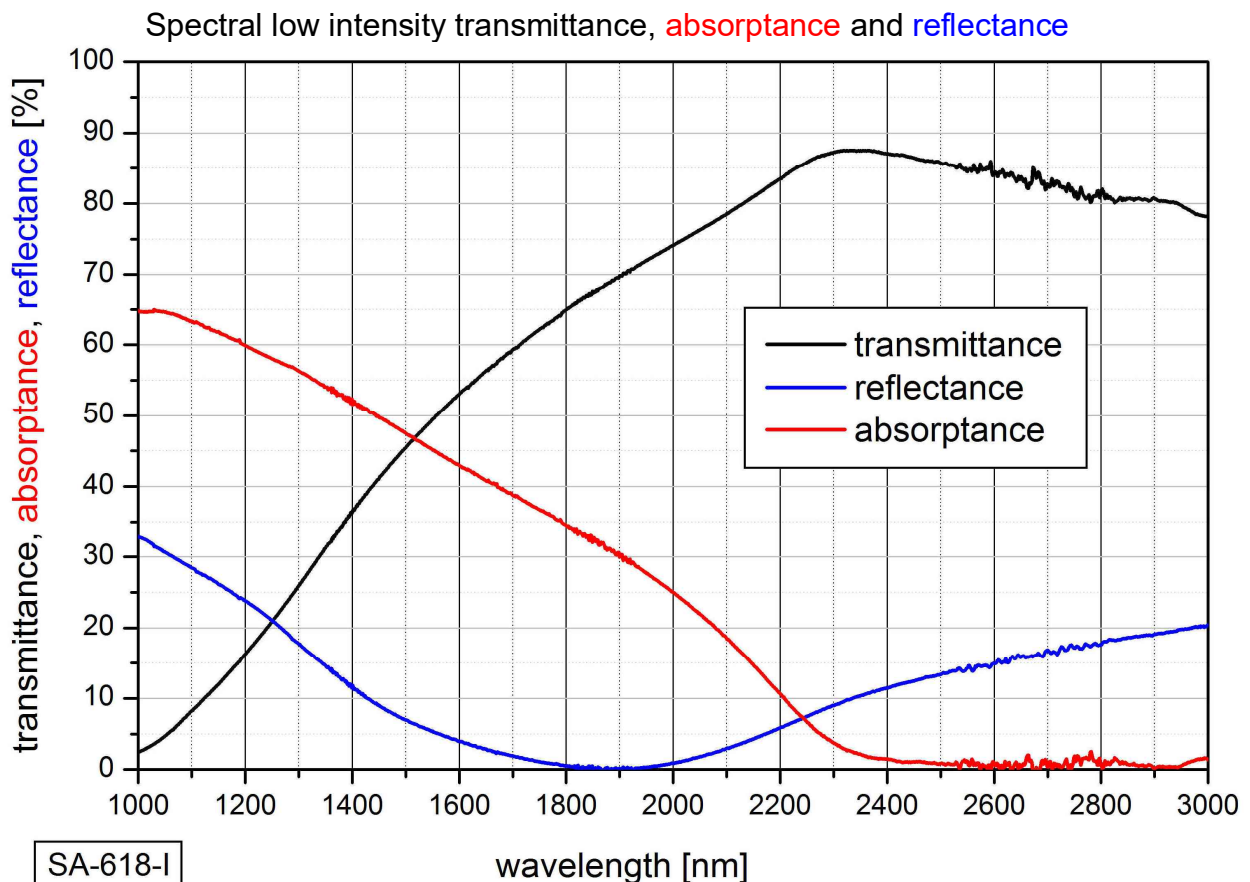
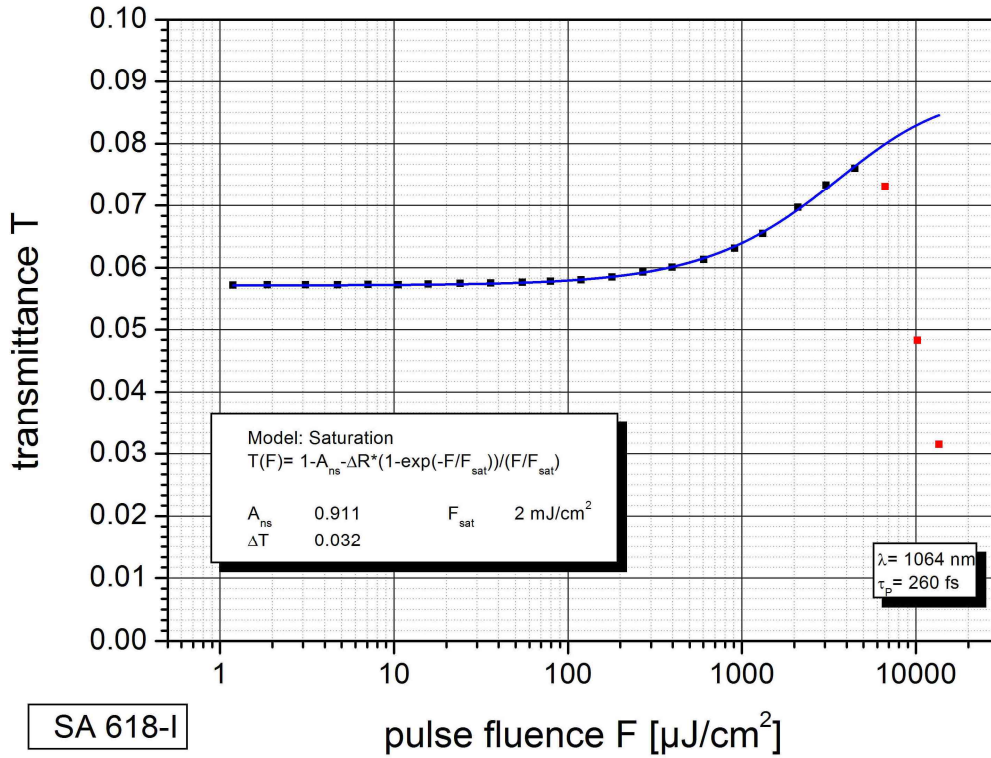


SA data sheet SA-2000-25-10ps-x, $\lambda = 2000 \text{ nm}$

Laser wavelength	$\lambda = 1800 \text{ nm} \dots 2200 \text{ nm}$
Absorptance	$A_0 = 25 \% @ 2000 \text{ nm}$
Transmittance	$T_0 = 74 \% @ 2000 \text{ nm}$
Reflectance	$R_0 = 1 \% @ 2000 \text{ nm}$
Modulation depth	$\Delta T = 15 \% @ 2000 \text{ nm}$
Non-saturable loss	$A_{ns} = 11 \% @ 2000 \text{ nm}$
Saturation fluence	$\Phi_{sat} = 2 \text{ mJ/cm}^2$
Damage threshold	$\Phi = 4 \text{ mJ/cm}^2$
Relaxation time constant	$\tau \sim 10 \text{ ps}$
Chip area	5.0 mm x 5.0 mm; other dimensions on request
Chip thickness	180 μm ; semi-insulating GaAs
Front side protection	AR coating for 2 μm
Back side coating	the SA back side is polished and antireflection coated for 2 μm
Mounting of SA-2000-25-10ps-x	denotes the type of mounting as follows:
x = 0	unmounted
x = 12.7 g	glued on a gilded Cu-cylinder with 12.7 mm \varnothing and 4 mm \varnothing center hole
x = 25.4 g	glued on a gilded Cu-cylinder with 25.4 mm \varnothing and 4 mm \varnothing center hole



Saturation measurement in transmission @ 1064 nm wavelength



Pump-probe measurement to determine the relaxation time @ 1064 nm wavelength

